

Recent Trend in Japanese Packaging Technology

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October 26, 2000 in Seoul

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Technological Topics under Development and in Pre-Production

- Various Wafer Level Packaging
- Chip Stacked High Density Devices
- Thin Package with Paper Thin Chips
- Extension of Flip Chip Interconnection
- Pb Free Soldering Adoption Roadmap
- Higher Density Built-up Substrate
- Finer Wiring Pattern for Redistribution
- Cu Plating Via Filling Mechanisms
- Substrate Materials Development

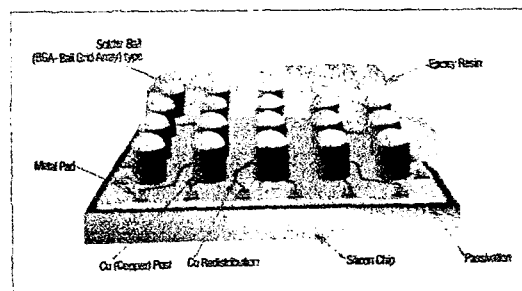
Next Generation Technology Development in Institutions

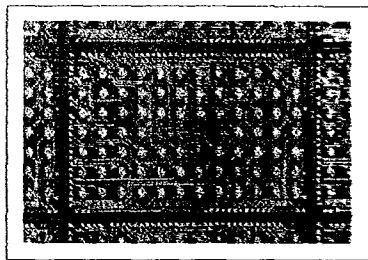
- 3D Chip Stacking with Chip Through Hole
- Optoelectronic Packaging
- Active Research Groups at Universities, Tokyo-U, Waseda-U, Shinshu-U, Okayama-U, Osaka-U
- Japan Institute of Electronics Packaging (JIEP-IMAPS Japan)
- Pb Free Soldering Development (NEDO-EIAJ-JEIDA)
- Super Connet Program (10 μ range technology)

Wafer Level Packaging- WLP

- WLP is aiming at lower device cost than CSP
- Redistribution is essential for peripheral pad chips
- Reliability is assured by resin coating
- Redistributed flip chip is WLP group
- MOST is growing
- New WLP company started
- Bumping business started

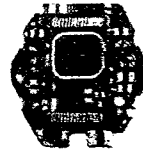
WLP CSP Post Structure (IEP)





Redistributed Wafer Level CSP showing Copper Posts

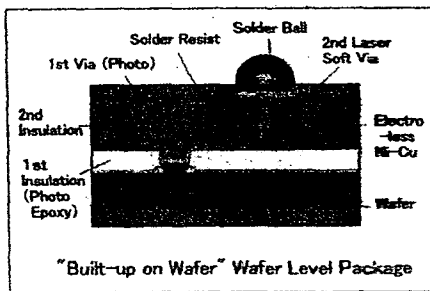
Application of WLP to Wrist Watch (Casio)



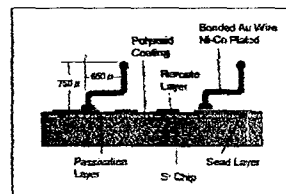
Conventional Wire Bond COB



WLP CSP Chip

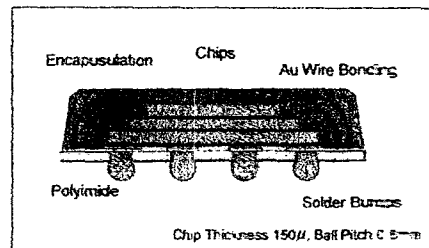


MOST (Microspring on Silicon Technology) by FormFactor and Shinko



Chip Level Stacking Device

- Mainly for Cellular phone
- Needed more memories
- 2-3 chip CSP by wire bonding or flip chip
- Low loop wire bonding
- Thickness is limited, 1.4mm
- Chips are ground to 50 μ
- Sharp, Toshiba, Fujitsu, Rohm, Epson
- ASET approach is chip through hole



3 Chip Stacking CSP Package by Sharp

Chip Through Hole Stacking 3D Package. ASET

Wafer through hole etching
Side wall CVD
Cu plating Cu filling
Dual Damascene CMP
Backside grinding
Bump formation

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Package Level Stacking Device

- 40-50 μ thick chips are packaged
- Device can be tested before stacking
- Dicing Before Grinding technology
- Grinding after packaging
- Au or solder bumps
- Total heights less than 150 μ
- Toshiba, NEC, Misuzu, Atomnics, Shinko, Ividen

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Package Level Stacking Device, Toshiba-Misuzu

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Cu Via Filling

- Vias are filled with Cu during plating
- Largely depends on additives and pulse current
- Important for cost reduction and surface flatness
- Several mechanisms proposed

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Cu Via Filling on Built-up Substrate (Shinko)

Plating Time: 10min.

Plating Time: 30min.

Plating Time: 50min.

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Built-up Substrate (6+4+6) by Shinko

Poly Phenylene Ether Layer for 250 μ Pitch Chips
 L/S=45 μ , Via Diameter=50 μ , Land=110 μ D electric=30 μ
 Vias are filled by Cu

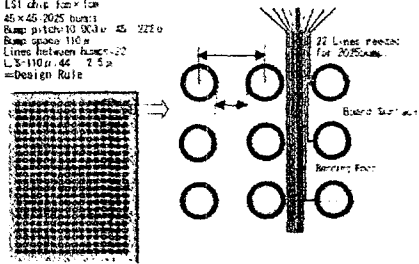
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Flip Chip Interconnection

- Bump pitch close to $150\ \mu$ (area), $60\ \mu$ (SBB)
- Microprocessor with C4 bumps and built-up substrate
- ACF and NCP connection and underfill
- SSB becoming more popular

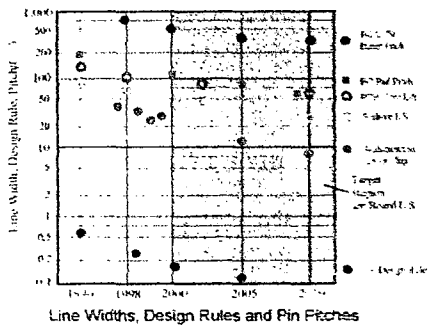
DEVIDA

LSI die footprint
 45×45 2025 bumps
 Bump pitch: $10\ 900\ \mu$ 45 2270
 Bump space: $110\ \mu$
 Lines between bumps: 22
 $L.S. = 110\ \mu \cdot 42 = 4.62\ \mu$
 = Design Rule



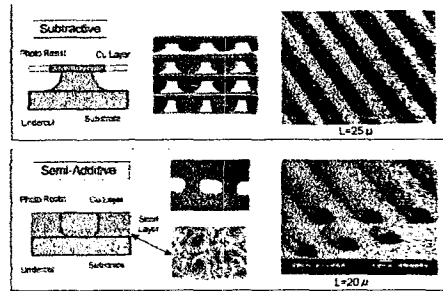
Fine Line Requirement on Board (one layer)

DEVIDA



Line Widths, Design Rules and Pin Pitches

DEVIDA



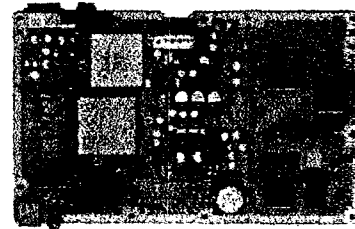
Fine Wiring Pattern Formation

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High Performance BGA

- Enhanced BGA with high speed signal and better thermal characteristics
- Double Layer tape interposer
- Metal heat spreader
- 800-1000 pins

DEVIDA



Playstation 2 (SCE-Toshiba)

CPU (Emotion Engine) Chip Size $11.02 \times 15.04\ \text{mm}$, 13,500 transistors
 $0.25\ \mu\text{Rule}$ CMOS, 300MHz, Vcc 1.6V, 5400pin EBGA
 Image Processor (Graphic Synthesizer) Chip Size $15.7 \times 16.7\ \text{mm}$ 2.25 μ
 Rule including 4MB DRAM, 32MB Direct Busbar

DEVIDA